REMARKS

No new matter has been added. Applicants request entry of the amendments as set forth herein prior to examination of the application on the merits.

Respectfully submitted,

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Enclosures: Version of Claims with Markings to Show Changes Made



VERSION OF CLAIMS WITH MARKINGS TO SHOW CHANGES MADE

- 5. (Amended) The structure of claim 1, wherein [a] the titanium lower portion of the nitrogen-rich Ti layer contains substantially no nitrogen.
 - 12. (Amended) A local interconnect structure, comprising:
- a semiconductor substrate;
- a titanium silicide layer disposed over a portion of the semiconductor substrate;
- a nitrogen-rich Ti layer disposed over the titanium silicide layer; and
- a refractory-metal silicide layer disposed on the nitrogen-rich Ti layer.

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